PRELIMINARY

Integrated Circuit Systems, Inc.

ICS85222

DUAL LVCMOS / LVTTL-TO-DIFFERENTIAL LVHSTL TRANSLATOR

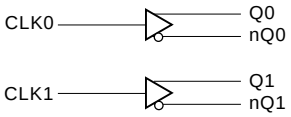
GENERAL DESCRIPTION

The ICS85222 is a Dual LVCMOS / LVTTL-to-Differential LVHSTL translator and a member of the HiPerClocks™ family of High Performance Clock Solutions from ICS. The ICS85222 has two single ended clock inputs. The single ended clock input accepts LVCMOS or LVTTL input levels and translates them to LVHSTL levels. The small outline 8-pin SOIC package makes this device ideal for applications where space, high performance and low power are important.

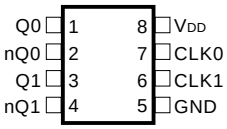
FEATURES

- 2 differential LVHSTL outputs
- Selectable CLK0, CLK1 LVCMOS clock inputs
- CLK0 and CLK1 can accept the following input levels: LVCMOS or LVTTL
- Maximum output frequency: 350MHz (typical)
- Part-to-part skew: TBD
- Propagation delay: 1.4ns (typical)
- V_{OH}: 1.2V (maximum)
- 3.3V operating supply voltage
- 0°C to 70°C ambient operating temperature
- Industrial temperature information available upon request

BLOCK DIAGRAM



PIN ASSIGNMENT



ICS85222
8-Lead SOIC
3.90mm x 4.92mm x 1.37mm body package
M Package
Top View

The Preliminary Information presented herein represents a product in prototyping or pre-production. The noted characteristics are based on initial product characterization. Integrated Circuit Systems, Incorporated (ICS) reserves the right to change any circuitry or specifications without notice.

TABLE 1. PIN DESCRIPTIONS

Number	Name	Type		Description
1, 2	Q0, nQ0	Output		Differential output pair. LVHSTL interface levels.
3, 4	Q1, nQ1	Output		Differential output pair. LVHSTL interface levels.
5	GND	Power		Power supply ground.
6	CLK1	Input	Pulldown	LVCMOS / LVTTL clock input.
7	CLK0	Input	Pulldown	LVCMOS / LVTTL clock input.
8	V_{DD}	Power		Positive supply pin. Connect to 3.3V.

NOTE: *Pulldown* refers to internal input resistors. See Table 2, Pin Characteristics, for typical values.
NOTE: Unused output pairs must be terminated.

TABLE 2. PIN CHARACTERISTICS

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C_{IN}	Input Capacitance				4	pF
R_{PULLUP}	Input Pullup Resistor			51		KΩ
$R_{PULLDOWN}$	Input Pulldown Resistor			51		KΩ

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V_{DD}	4.6V
Inputs, V_I	-0.5V to V_{DD} + 0.5V
Outputs, V_O	-0.5V to V_{DD} + 0.5V
Package Thermal Impedance, θ_{JA}	112.7°C/W (0 lfpm)

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

TABLE 3A. POWER SUPPLY DC CHARACTERISTICS, V_{DD} = 3.3V±5%, T_A = 0°C TO 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Positive Supply Voltage		3.135	3.3	3.465	V
I_{DD}	Power Supply Current			32		mA

TABLE 3B. LVCMOS / LVTTL DC CHARACTERISTICS, V_{DD} = 3.3V±5%, T_A = 0°C TO 70°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage	CLK0, CLK1		2		V_{DD} + 0.3	V
V_{IL}	Input Low Voltage	CLK0, CLK1		-0.3		1.3	V
I_{IH}	Input High Current	CLK0, CLK1	$V_{DD} = V_{IN}$ = 3.465V			150	µA
I_{IL}	Input Low Current	CLK0, CLK1	$V_{DD} = V_{IN}$ = 3.465V	-5			µA

TABLE 3C. LVHSTL DC CHARACTERISTICS, V_{DD} = 3.3V±5%, T_A = 0°C TO 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OH}	Output High Voltage; NOTE 1		1		1.2	V
V_{OL}	Output Low Voltage; NOTE 1		0		0.4	V
V_{OX}	Output Crossover Voltage		40% x (V_{OH}-V_{OL}) + V_{OL}		60% x (V_{OH}-V_{OL}) + V_{OL}	V
V_{SWING}	Peak-to-Peak Output Voltage Swing		0.6		1.2	V

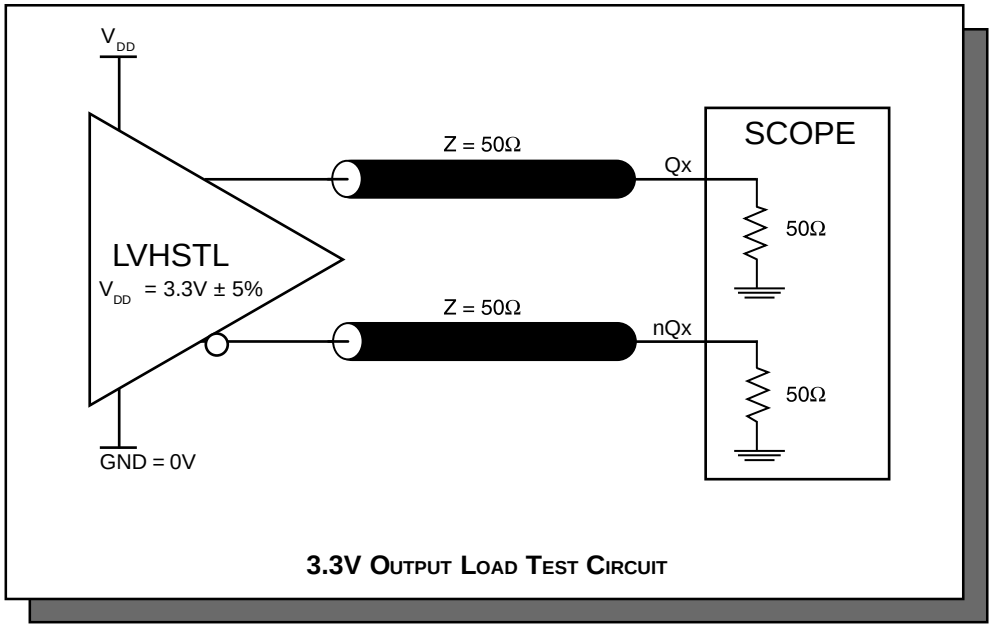
NOTE 1: Outputs terminated with 50Ω to GND.

TABLE 4. AC CHARACTERISTICS, V_{DD} = 3.3V±5%, T_A = 0°C TO 70°C

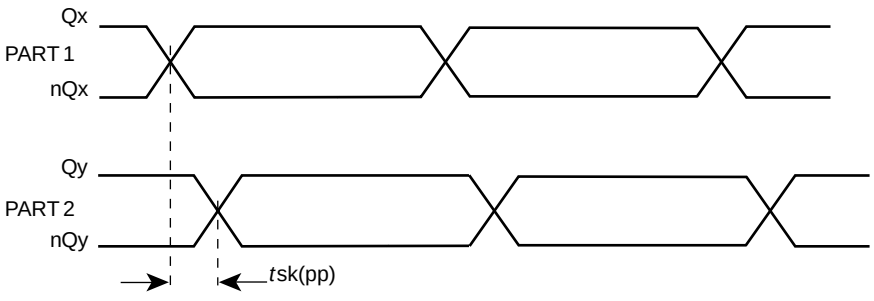
Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency			350		MHz
t_{PD}	Propagation Delay; NOTE 1	$f \leq$ 350MHz		1.4		ns
*t*sk(pp)	Part-to-Part Skew; NOTE 2, 3			TBD		ps
t_R	Output Rise Time	20% to 80%		400		ps
t_F	Output Fall Time	20% to 80%		400		ps
odc	Output Duty Cycle			50		%

All parameters measured at f_{MAX} unless noted otherwise.
NOTE 1: Measured from $V_{DD}/2$ of the input to the differential output crossing point.
NOTE 2: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross points.
NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

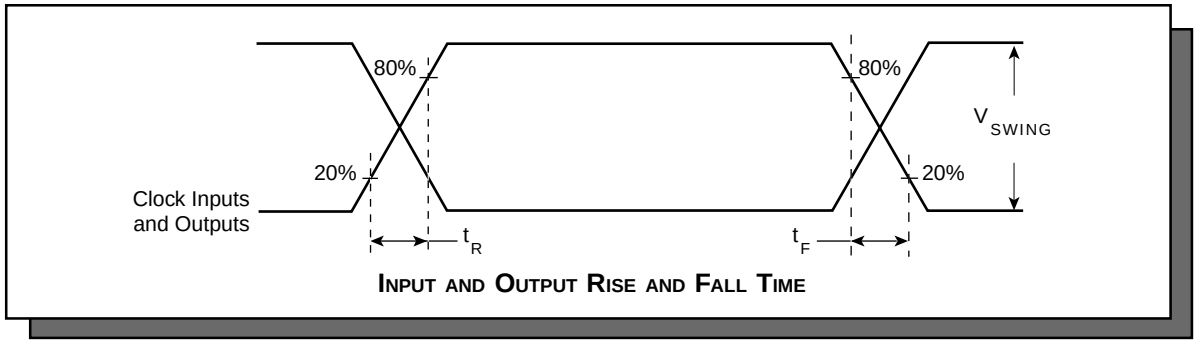
PARAMETER MEASUREMENT INFORMATION



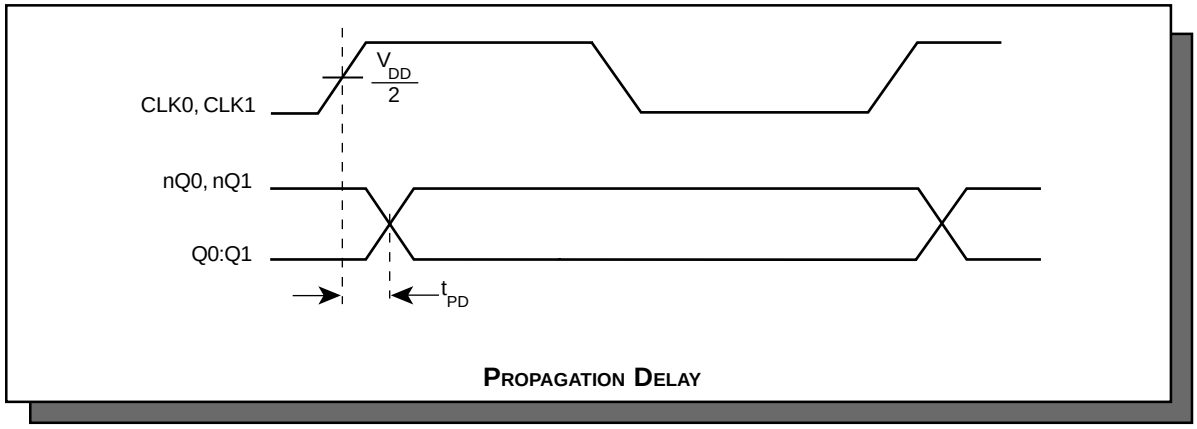
3.3V OUTPUT LOAD TEST CIRCUIT



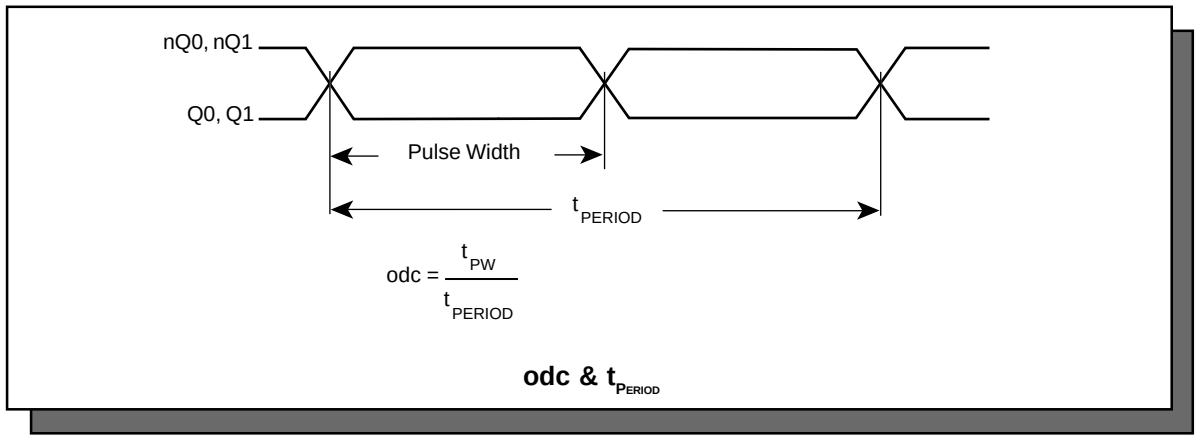
PART-TO-PART SKEW



INPUT AND OUTPUT RISE AND FALL TIME



PROPAGATION DELAY



odc & t_{PERIOD}

POWER CONSIDERATIONS

This section provides information on power dissipation and junction temperature for the ICS85222.
Equations and example calculations are also provided.

1. Power Dissipation.
The total power dissipation for the ICS85222 is the sum of the core power plus the power dissipated in the load(s).
The following is the power dissipation for V_{DD} = 3.3V + 5% = 3.465V, which gives worst case results.
NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)$_{MAX}$ = V_{DD_MAX} * I_{DD_MAX} = 3.465V * 32mA = **111mW**
- Power (outputs)$_{MAX}$ = **32.8mW/Loaded Output pair**
  If all outputs are loaded, the total power is 2 * 78.9mW = **157.8mW**

Total Power$_{_MAX}$ (3.465V, with all outputs switching) = 111mW + 157.8mW = **268.8mW**

2. Junction Temperature.
Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature for HiPerClockS™ devices is 125°C.

The equation for Tj is as follows: $Tj = \theta_{JA} * Pd\_total + T_A$

Tj = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in Section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming a moderate air flow of 200 linear feet per minute and a multi-layer board, the appropriate value is 103.3°C/W per Table 5 below. Therefore, Tj for an ambient temperature of 70°C with all outputs switching is:

70°C + 0.269W * 103.3°C/W = 98°C. This is well below the limit of 125°C

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow, and the type of board (single layer or multi-layer).

TABLE 5. THERMAL RESISTANCE θ_{JA} FOR 8-PIN SOIC, FORCED CONVECTION

θ_{JA} by Velocity (Linear Feet per Minute)	0	200	500
Single-Layer PCB, JEDEC Standard Test Boards	153.3°C/W	128.5°C/W	115.5°C/W
Multi-Layer PCB, JEDEC Standard Test Boards	112.7°C/W	103.3°C/W	97.1°C/W

NOTE: Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs.

3. Calculations and Equations.

The purpose of this section is to derive the power dissipated into the load.

LVHSTL output driver circuit and termination are shown in *Figure 1.*

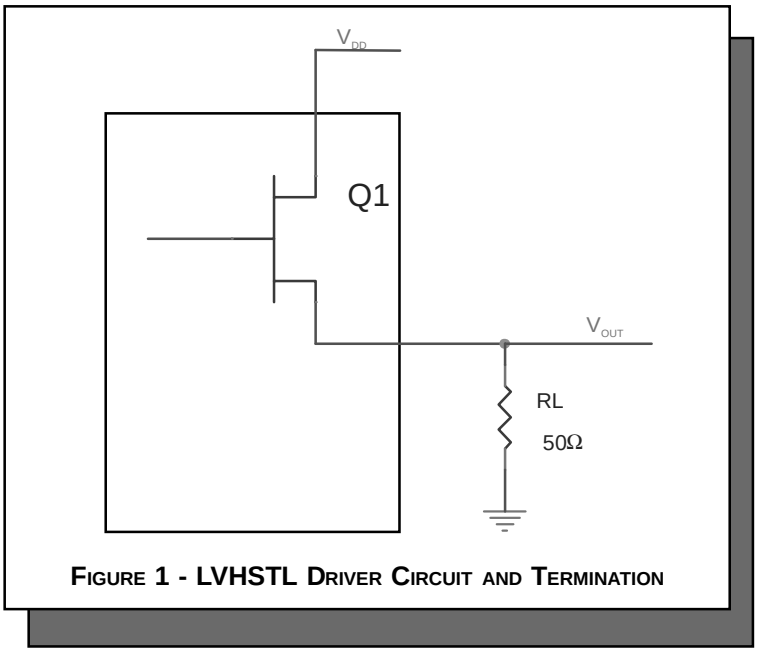


FIGURE 1 - LVHSTL DRIVER CIRCUIT AND TERMINATION

To calculate worst case power dissipation into the load, use the following equations which assume a 50Ω load.

Pd_H is power dissipation when the output drives high.
Pd_L is the power dissipation when the output drives low.

$Pd\_H = (V_{OH\_MIN}/R_L) * (V_{DD\_MAX} - V_{OH\_MIN})$

$Pd\_L = (V_{OL\_MAX}/R_L) * (V_{DD\_MAX} - V_{OL\_MAX})$

Pd_H = (1.2V/50Ω) * (3.465V - 1.2V) = **54.4mW**
Pd_L = (0.4V/50Ω) * (3.465V - 0.4V) = **24.52mW**

Total Power Dissipation per output pair = Pd_H + Pd_L = **78.9mW**

RELIABILITY INFORMATION

TABLE 6. θ_{JA} VS. AIR FLOW TABLE

θ_{JA} by Velocity (Linear Feet per Minute)			
	0	**200**	**500**
Single-Layer PCB, JEDEC Standard Test Boards	153.3°C/W	128.5°C/W	115.5°C/W
Multi-Layer PCB, JEDEC Standard Test Boards	112.7°C/W	103.3°C/W	97.1°C/W

NOTE: Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs.

TRANSISTOR COUNT

The transistor count for ICS85222 is: 443

PACKAGE OUTLINE - M SUFFIX

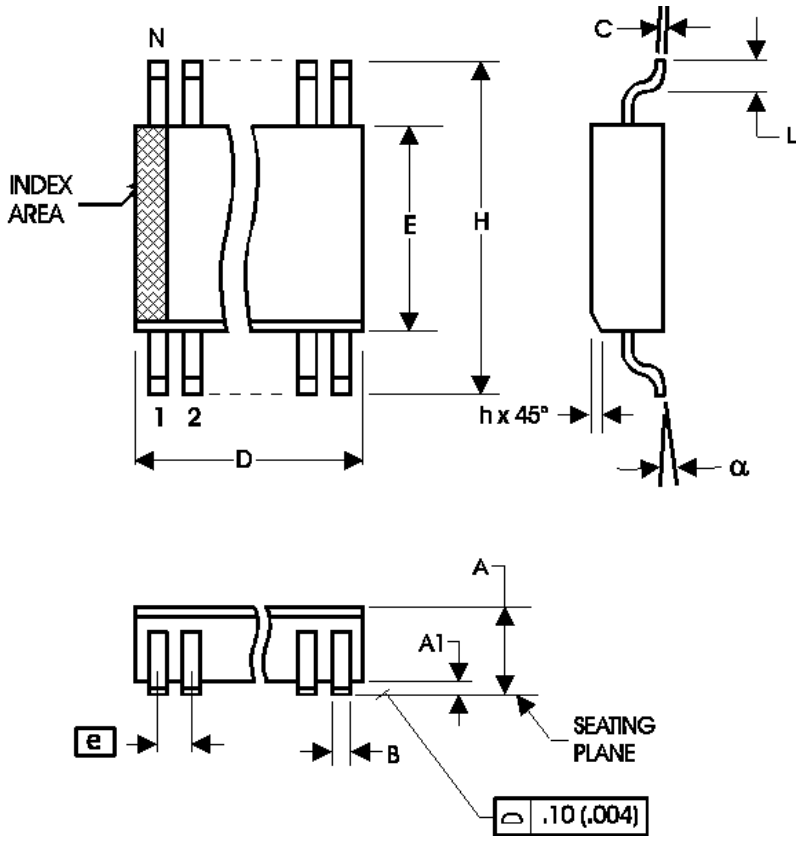


TABLE 7. PACKAGE DIMENSIONS

SYMBOL	Millimeters	
	MINIMUM	MAXIMUM
N	8	
A	1.35	1.75
A1	0.10	0.25
B	0.33	0.51
C	0.19	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27 BASIC	
H	5.80	6.20
h	0.25	0.50
L	0.40	1.27
α	0°	8°

Reference Document: JEDEC Publication 95, MS-012

TABLE 8. ORDERING INFORMATION

Part/Order Number	Marking	Package	Count	Temperature
ICS85222AM	85222AM	8 lead SOIC	96 per tube	0°C to 70°C
ICS85222AMT	85222AM	8 lead SOIC on Tape and Reel	2500	0°C to 70°C